



Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



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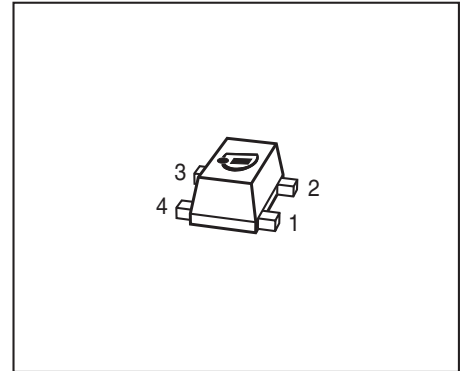
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Low Noise Silicon Bipolar RF Transistor

- For highest gain and low noise amplifier
Outstanding $G_{ms} = 22.5$ dB at 1.8 GHz
Minimum noise figure $NF_{min} = 0.95$ dB at 1.8 GHz
- For oscillators up to 15 GHz
- Transition frequency $f_T = 45$ GHz
- Pb-free (RoHS compliant) and halogen-free thin small flat package with visible leads
- Qualification report according to AEC-Q101 available



ESD (Electrostatic discharge) sensitive device, observe handling precaution!

Type	Marking	Pin Configuration						Package
BFP520F	APs	1=B	2=E	3=C	4=E	-	-	TSFP-4

Maximum Ratings at $T_A = 25$ °C, unless otherwise specified

Parameter	Symbol	Value	Unit
Collector-emitter voltage $T_A = 25$ °C $T_A = -55$ °C	V_{CEO}	2.5 2.4	V
Collector-emitter voltage	V_{CES}	10	
Collector-base voltage	V_{CBO}	10	
Emitter-base voltage	V_{EBO}	1	
Collector current	I_C	50	mA
Base current	I_B	5	
Total power dissipation ¹⁾ $T_S \leq 98$ °C	P_{tot}	120	mW
Junction temperature	T_J	150	°C
Storage temperature	T_{Stg}	-55 ... 150	

¹⁾ T_S is measured on the emitter lead at the soldering point to pcb

Thermal Resistance

Parameter	Symbol	Value	Unit
Junction - soldering point ¹⁾	R_{thJS}	430	K/W

Electrical Characteristics at $T_A = 25\text{ °C}$, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
DC Characteristics					
Collector-emitter breakdown voltage $I_C = 1\text{ mA}, I_B = 0$	$V_{(BR)CEO}$	2.5	3	3.5	V
Collector-emitter cutoff current $V_{CE} = 10\text{ V}, V_{BE} = 0$	I_{CES}	-	-	10	μA
Collector-base cutoff current $V_{CB} = 5\text{ V}, I_E = 0$	I_{CBO}	-	-	200	mA
Emitter-base cutoff current $V_{EB} = 1\text{ V}, I_C = 0$	I_{EBO}	-	-	35	μA
DC current gain $I_C = 20\text{ mA}, V_{CE} = 2\text{ V}$, pulse measured	h_{FE}	70	110	170	-

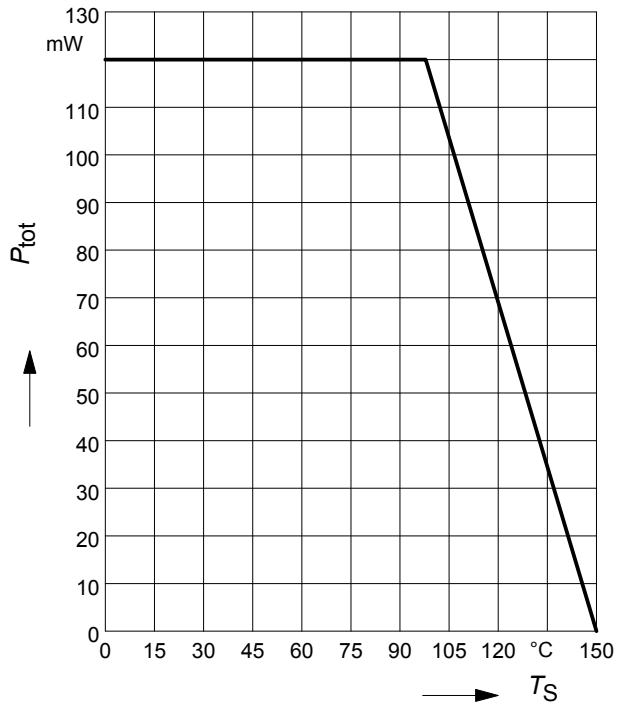
¹For the definition of R_{thJS} please refer to Application Note AN077 (Thermal Resistance Calculation)

Electrical Characteristics at $T_A = 25\text{ }^\circ\text{C}$, unless otherwise specified

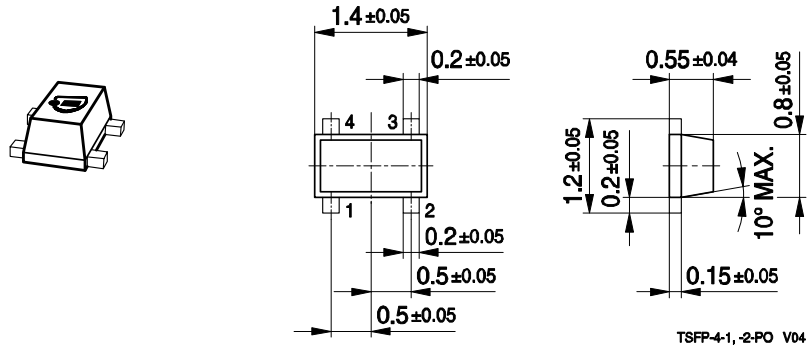
Parameter	Symbol	Values			Unit
		min.	typ.	max.	
AC Characteristics (verified by random sampling)					
Transition frequency $I_C = 30\text{ mA}$, $V_{CE} = 2\text{ V}$, $f = 2\text{ GHz}$	f_T	32	45	-	GHz
Collector-base capacitance $V_{CB} = 2\text{ V}$, $f = 1\text{ MHz}$, $V_{BE} = 0$, emitter grounded	C_{cb}	-	0.07	0.14	pF
Collector emitter capacitance $V_{CE} = 2\text{ V}$, $f = 1\text{ MHz}$, $V_{BE} = 0$, base grounded	C_{ce}	-	0.25	-	
Emitter-base capacitance $V_{EB} = 0.5\text{ V}$, $f = 1\text{ MHz}$, $V_{CB} = 0$, collector grounded	C_{eb}	-	0.31	-	
Minimum noise figure $I_C = 2\text{ mA}$, $V_{CE} = 2\text{ V}$, $Z_S = Z_{Sopt}$, $f = 1.8\text{ GHz}$	NF_{min}	-	0.95	-	dB
Power gain, maximum stable ¹⁾ $I_C = 20\text{ mA}$, $V_{CE} = 2\text{ V}$, $Z_S = Z_{Sopt}$, $Z_L = Z_{Lopt}$, $f = 1.8\text{ GHz}$	G_{ms}	-	22.5	-	dB
Insertion power gain $V_{CE} = 2\text{ V}$, $I_C = 20\text{ mA}$, $f = 1.8\text{ GHz}$, $Z_S = Z_L = 50\text{ }\Omega$	$ S_{21} ^2$	-	20.5	-	
Third order intercept point at output $V_{CE} = 2\text{ V}$, $I_C = 20\text{ mA}$, $f = 1.8\text{ GHz}$, $Z_S = Z_{Sopt}$, $Z_L = Z_{Lopt}$	$IP3$	-	23.5	-	dBm
1dB compression point $I_C = 20\text{ mA}$, $V_{CE} = 2\text{ V}$, $Z_S = Z_{Sopt}$, $Z_L = Z_{Lopt}$, $f = 1.8\text{ GHz}$	P_{-1dB}	-	10.5	-	

¹⁾ $G_{ms} = |S_{21} / S_{12}|$

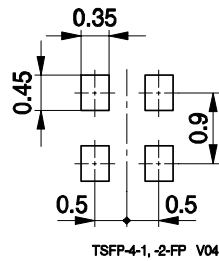
Total power dissipation $P_{\text{tot}} = f(T_S)$



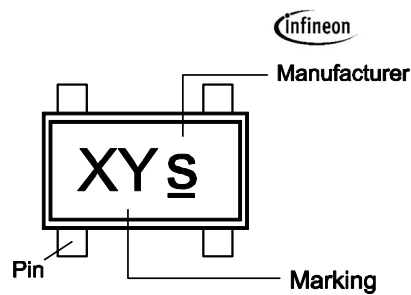
Package Outline



Foot Print

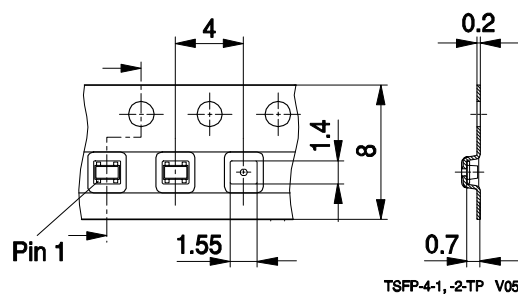


Marking Layout (Example)



Standard Packing

Reel \varnothing 180 mm = 3.000 Pieces/Reel
 Reel \varnothing 330 mm = 10.000 Pieces/Reel



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